

**In the Claims**

Claims 1-88 are canceled.

89. [Previously Presented] A method of processing a wafer comprising:  
receiving a wafer within a workpiece processing apparatus;  
supporting the wafer using a workpiece holder of the workpiece processing apparatus;  
coupling circuitry of the wafer with circuitry of the workpiece holder;  
exposing the wafer within the workpiece processing apparatus to process conditions usable to form at least one semiconductor device; and  
communicating signals intermediate the circuitry of the wafer and the circuitry of the workpiece holder.

90. [Previously Presented] The method in accordance with claim 89 wherein the coupling comprises coupling the circuitry of the wafer and the circuitry of the workpiece holder at a surface of the wafer and a surface of the workpiece holder.

91. [Previously Presented] The method in accordance with claim 89 wherein the receiving comprises receiving a semiconductive wafer.

92. [Previously Presented] The method in accordance with claim 89 further comprising altering the process conditions responsive to the communicating.

93. [Previously Presented] The method in accordance with claim 89 wherein the communicating comprises communicating during the processing of a production workpiece.

94. [Previously Presented] The method in accordance with claim 89 further comprising communicating the signals using an intermediate member of the workpiece processing apparatus.

95. [Previously Presented] The method in accordance with claim 89 wherein the coupling comprises contacting the circuitry of the wafer and the circuitry of the workpiece holder.

96. [Previously Presented] The method in accordance with claim 89 wherein the communicating comprises communicating the signals comprising information.

97. [Previously Presented] The method in accordance with claim 89 wherein the communicating comprises communicating the signals comprising information regarding the process conditions.

98. [Previously Presented] A method of processing a workpiece comprising:  
receiving a first workpiece and a second workpiece within a workpiece processing apparatus configured to form a semiconductor device using the first workpiece;  
processing the first workpiece within the workpiece processing apparatus to form the semiconductor device; and  
communicating signals intermediate the second workpiece and the workpiece processing apparatus.

99. [Previously Presented] The method in accordance with claim 98 further comprising electrically coupling the second workpiece and the workpiece processing apparatus.

100. [Previously Presented] The method in accordance with claim 99 wherein the coupling comprises contacting circuitry of the second workpiece and circuitry of the apparatus.

101. [Previously Presented] The method in accordance with claim 98 further comprising:

supporting the second workpiece using a workpiece holder of the workpiece processing apparatus; and

coupling circuitry of the second workpiece and circuitry of the workpiece holder at a surface of the second workpiece and a surface of the workpiece holder.

102. [Previously Presented] The method in accordance with claim 98 wherein the receiving comprises receiving the first workpiece comprising a semiconductive wafer.

103. [Previously Presented] The method in accordance with claim 98 further comprising altering the processing responsive to the communicating.

104. [Previously Presented] The method in accordance with claim 98 wherein the communicating comprises communicating during the processing.

105. [Previously Presented] The method in accordance with claim 98 further comprising communicating the signals using an intermediate member of the workpiece processing apparatus.

106. [Previously Presented] The method in accordance with claim 98 wherein the communicating comprises communicating the signals comprising information.

107. [Previously Presented] The method in accordance with claim 98 wherein the communicating comprises communicating the signals comprising information regarding the processing.

108. [Previously Presented] A method of communicating signals with respect to a wafer comprising:

providing a workpiece holder;

supporting a wafer using the workpiece holder;

coupling circuitry of the wafer with circuitry of the workpiece holder; and

communicating signals intermediate the circuitry of the wafer and the circuitry of the workpiece holder.

109. [Previously Presented] The method in accordance with claim 108 wherein the providing the wafer comprises providing a semiconductive wafer.

110. [Previously Presented] The method in accordance with claim 108 wherein the coupling comprises coupling the circuitry of the wafer and the circuitry of the workpiece holder at a surface of the wafer and a surface of the workpiece holder.

111. [Previously Presented] The method in accordance with claim 108 wherein the coupling comprises contacting the circuitry of the wafer and the circuitry of the workpiece holder.

112. [Previously Presented] The method in accordance with claim 108 wherein the communicating comprises communicating using an intermediate member.

113. [Previously Presented] The method in accordance with claim 108 wherein the communicating comprises communicating the signals comprising information.

114. [Previously Presented] The method in accordance with claim 108 wherein the communicating comprises communicating the signals comprising information regarding process conditions of a workpiece processing apparatus.

115. [Previously Presented] A method of communicating signals within a workpiece processing apparatus comprising:

providing a workpiece processing apparatus adapted to form a semiconductor device;

providing a workpiece within the workpiece processing apparatus;

communicating signals using the workpiece; and

receiving the signals within the workpiece processing apparatus from the workpiece.

116. [Previously Presented] The method in accordance with claim 115 further comprising coupling circuitry of the workpiece with circuitry of the workpiece processing apparatus.

117. [Previously Presented] The method in accordance with claim 116 wherein the coupling comprises contacting the circuitry of the workpiece with the circuitry of the workpiece processing apparatus.

118. [Previously Presented] The method in accordance with claim 116 further comprising breaking the coupling of the circuitry of the workpiece and the circuitry of the workpiece processing apparatus.

119. [Previously Presented] The method in accordance with claim 115 further comprising supporting the workpiece within the workpiece processing apparatus using a workpiece holder, and wherein the receiving comprises receiving using the workpiece holder.

120. [Previously Presented] The method in accordance with claim 119 further comprising coupling circuitry of the workpiece and circuitry of the workpiece holder at a surface of the workpiece and a surface of the workpiece holder.

121. [Previously Presented] The method in accordance with claim 115 further comprising supporting the workpiece within the workpiece processing apparatus using a workpiece holder and an intermediate member, and wherein the receiving comprises receiving using the workpiece holder and the intermediate member.

122. [Previously Presented] The method in accordance with claim 115 wherein the providing the workpiece comprises providing a semiconductive wafer.

123. [Previously Presented] The method in accordance with claim 115 wherein the communicating comprises communicating the signals comprising information.

124. [Previously Presented] The method in accordance with claim 115 wherein the communicating comprises communicating the signals comprising information regarding process conditions of the workpiece processing apparatus.

125. [Previously Presented] The method in accordance with claim 89 wherein the circuitry of the wafer comprises an electrical coupling at a surface of the wafer.

126. [Previously Presented] The method in accordance with claim 89 wherein the wafer comprises a calibration workpiece.

127. [Previously Presented] The method in accordance with claim 89 further comprising originating the signals using the circuitry of the wafer.

128. [Previously Presented] The method in accordance with claim 98 wherein the first workpiece comprises a production workpiece and the second workpiece comprises a calibration workpiece.



129. [Previously Presented] The method in accordance with claim 108 wherein the supporting the wafer comprises supporting the wafer comprising a calibration workpiece.

130. [Previously Presented] The method in accordance with claim 115 wherein the providing comprises providing the workpiece comprising a calibration workpiece.

131. [Previously Presented] The method in accordance with claim 115 further comprises exposing the workpiece to process conditions configured to form the semiconductor device.

132. [Previously Presented] The method in accordance with claim 131 wherein the workpiece processing apparatus is adapted to form the semiconductor device from a production workpiece.

133. [New] The method in accordance with claim 115 wherein the receiving comprises receiving the signals comprising information using circuitry of the workpiece processing apparatus.

134. [New] The method in accordance with claim 115 wherein the communicating comprises communicating the signals comprising process signals comprising information regarding process conditions of the workpiece processing apparatus used to form the semiconductor device.

135. [New] The method in accordance with claim 115 wherein the communicating comprises communicating the signals comprising process signals comprising information regarding a temperature of a surface of the workpiece.

136. [New] The method in accordance with claim 115 wherein the communicating comprises communicating the signals comprising process signals comprising information regarding temperature information at a plurality of different positions of a surface of the workpiece.